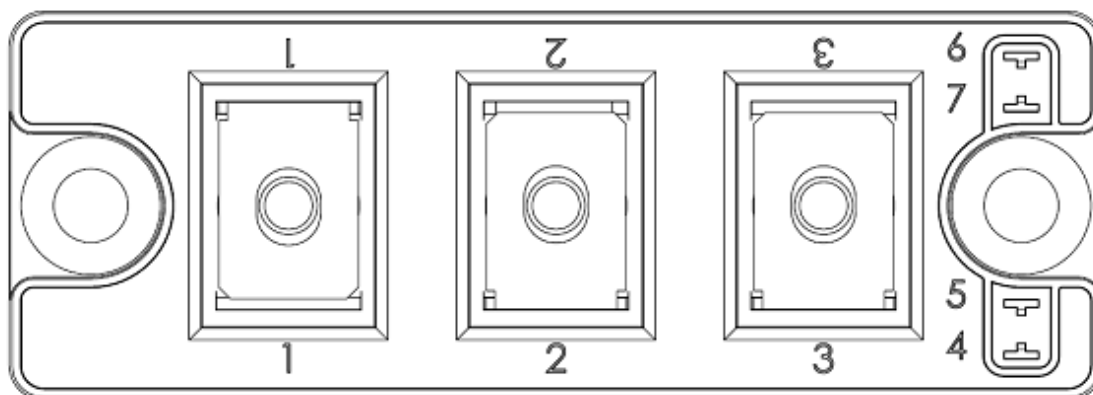
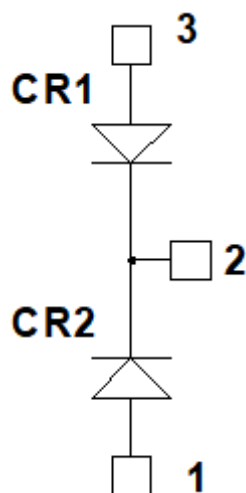


MSCDC200KK120D1PAG Dual Common Cathode SiC Diodes Power Module

1 Product Overview

This section shows the product overview of the MSCDC200KK120D1PAG device.



All ratings at $T_j = 25^\circ\text{C}$, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

1.1 Features

The following are key features of the MSCDC200KK120D1PAG device:

- Silicon carbide (SiC) Schottky diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature-independent switching behavior
 - Positive temperature coefficient on VF
- M5 power connectors
- Aluminum nitride (AlN) substrate for improved thermal performance

1.2 Benefits

The following are benefits of the MSCDC200KK120D1PAG device:

- Stable temperature behavior
- Low losses
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

1.3 Applications

The MSCDC200KK120D1PAG device is designed for the following applications:

- Welding converters
- Switched Mode power supplies
- Uninterrupted power supplies
- Motor control

2 Electrical Specifications

This section shows the electrical specifications of the MSCDC200KK120D1PAG device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode of the MSCDC200KK120D1PAG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Maximum Ratings	Unit
V_{RRM}	Repetitive peak reverse voltage	1200	V
I_F	DC forward current	$T_C = 95\text{ }^{\circ}\text{C}$ 200	A

The following table shows the thermal and package characteristics of the MSCDC200KK120D1PAG.

Table 2 • Thermal and Package Characteristics

Symbol	Characteristic			Min	Max	Unit
V _{ISOL}	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz			4000		V
T _J	Operating junction temperature range			−40	175	°C
T _{JOP}	Recommended junction temperature under switching conditions			−40	T _{Jmax} − 25	
T _{STG}	Storage temperature range			−40	125	
T _C	Operating case temperature			−40	125	
Torque	Mounting torque	For terminals	M5	2	3.5	N.m
		To Heatsink	M6	3	5	
Wt	Package weight				160	g

2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSCDC200KK120D1PAG.

Table 3 • Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode forward voltage	$I_F = 200\text{ A}$	$T_J = 25\text{ }^{\circ}\text{C}$	1.5	1.8	V
			$T_J = 175\text{ }^{\circ}\text{C}$	2.1		
I_{RM}	Reverse leakage current	$V_R = 1200\text{ V}$	$T_J = 25\text{ }^{\circ}\text{C}$	60	800	μA
			$T_J = 175\text{ }^{\circ}\text{C}$	1000		
Q_C	Total capacitive charge	$V_R = 600\text{ V}$		896		nC
C	Total capacitance	$f = 1\text{ MHz}, V_R = 400\text{ V}$		984		pF
		$f = 1\text{ MHz}, V_R = 800\text{ V}$		728		
R_{thJC}	Junction-to-case thermal resistance				0.16	$^{\circ}\text{C/W}$

2.3 Performance Curves

This section shows the typical performance curves for the MSCDC200KK120D1PAG device.

Figure 1 • Maximum Transient Thermal Impedance

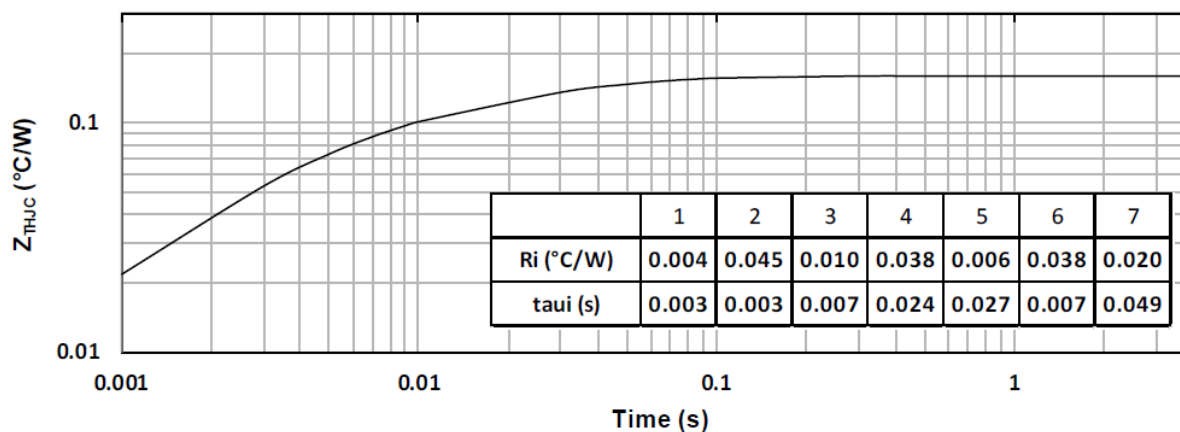


Figure 2 • Forward Current vs. Forward Voltage

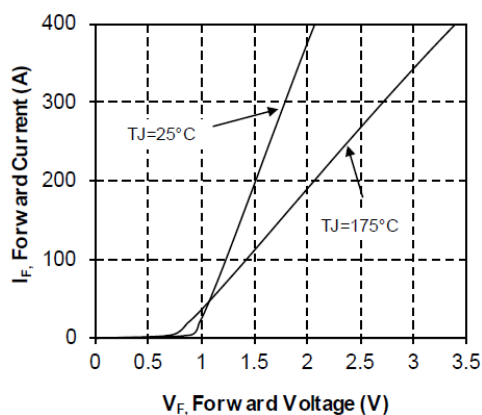
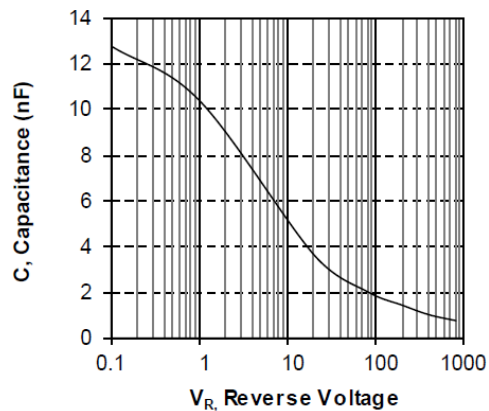


Figure 3 • Capacitance vs. Reverse Voltage



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